MCH2005F



MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit	
Collector-Emitter Voltage	VCEO	30	Vdc	
Collector-Base Voltage	V _{CB}	50	Vdc	
Emitter-Base Voltage	VEB	7.0	Vdc	
Collector Current – Continuous	IC.	6.0	Adc	
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $T_A = 25^{\circ}C$	PD	500 2.86	mW mW/ ^o C	
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above $T_A = 25^{\circ}C$	PD	5.0 28.6	Watts mW/ ⁰ C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C	



This is advance information and specifications are subject to change without notice. See Packaging Information Section for outline dimensions.

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage* (I _C = 10 mAdc)	BVCEO	30	_	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 µAdc)	BVEBO	7.0	_	Vdc
Collector Cutoff Current {V _{CB} = 50 Vdc}	СВО	-	2.0	μAdc
ON CHARACTERISTICS				
DC Current Gain* (I _C = 1.0 Adc, V _{CE} = 10 Vdc) (I _C = 5.0 Adc, V _{CE} = 10 Vdc)	hfe*	1000	Ξ	-
Collector-Emitter Saturation Voltage* ($I_C = 1.0 \text{ Adc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 5.0 \text{ Adc}$, $I_B = 5.0 \text{ mAdc}$)	VCE(sat)*	-	1.2 2.5	Vdc
Base-Emitter Saturation Voltage" (I _C = 1.0 Adc, I _B = 1.0 mAdc) (I _C = 5.0 Adc, I _B = 5.0 mAdc)	VBE(sat)*		1.5 3.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain-Bandwidth Product (I _E = 100 mAdc, V _{CE} = 10 Vdc)	fT	100	_	MHz
SWITCHING CHARACTERISTICS	. Que			
Turn-On Time* (V _{CC} = 6.75 Vdc, I _C = 5.0 Adc, I _B = 5.0 mAdc) Figure 1	ton*	-	350	ns
Turn-Off Time* (V _{CC} = 6.75 Vdc, I _C = 5.0 Adc, I _B = 5.0 mAdc) Figure 1	toff*	-	450	ns

*Pulse Test: Pulse Width $\leq 2.0 \ \mu$ s, Duty Cycle $\leq 2.0\%$.

